

## WHAT IS CLAIMED IS:

1. A method of manufacturing an EDMOS device having a lattice type drift region, comprising the steps of:

forming a well region in a given region of a silicon substrate;

alternately implanting first impurity ions in a given region of said well region to form a lattice type drift region having a first lattice and a second lattice which are alternately arranged, wherein said first lattice is implanted by said first impurity ions;

forming a field oxide film on a given region of said silicon substrate;

implanting second impurity ions in said well region to control a threshold voltage;

forming a gate insulating film and a polysilicon film on said silicon substrate of said well region, and then patterning said polysilicon film to form a gate electrode;

implanting third impurity ions in said well region and said drift region to form a source region and a drain region, respectively;

implanting fourth impurity ions in said well region to form a source contact region connected to said source region;

forming an insulating film on an entire structure, and then forming contact holes in said insulating film to expose said source region, said drain region and said gate electrode; and

forming metal wires connected to said source region, said drain region and said gate electrode via said contact holes, respectively.

2. The method of manufacturing the EDMOS device as claimed in claim 1, wherein a concentration of said first lattice is higher than that of said second lattice.